Kingbright

PHOTOTRANSISTOR

Part Number: KM-4457P3C

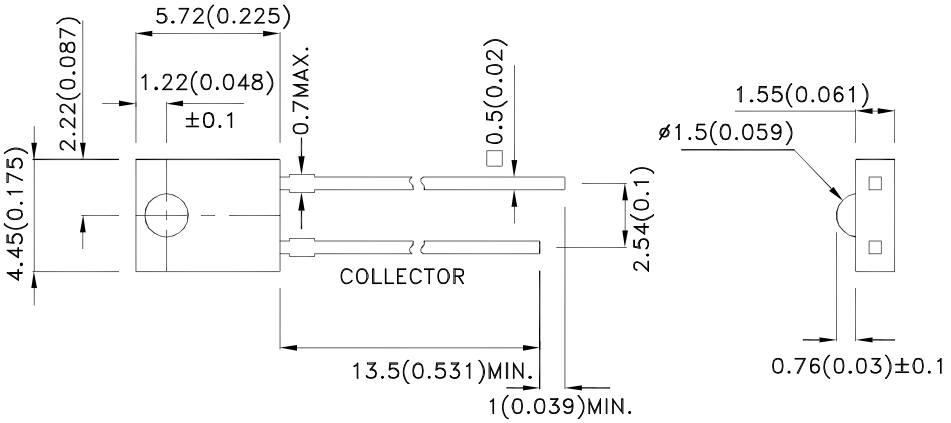
Features

- Mechanically and spectrally matched to infrared emitting LED lamp.
- RoHS compliant.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



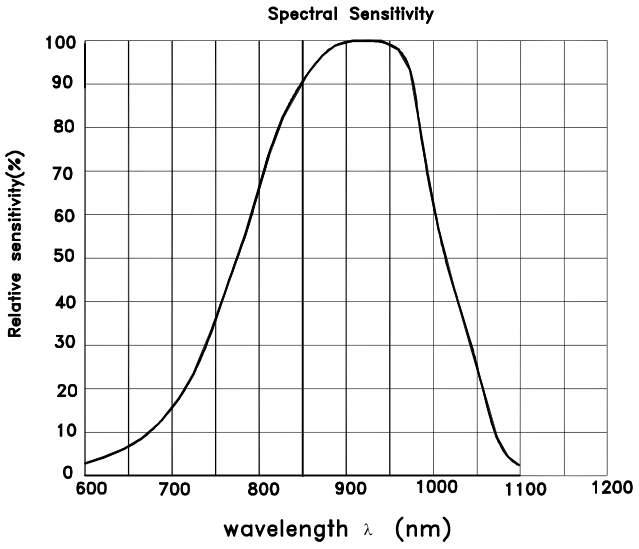
Notes:
1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{BR\ CEO}$	Collector-to-Emitter Breakdown Voltage	30			V	I_C=100uA Ee=0mW/c㎡
$V_{BR\ ECO}$	Emitter-to-Collector Breakdown Voltage	5			V	I_E=100uA Ee=0mW/c㎡
$V_{CE\ (SAT)}$	Collector-to-Emitter Saturation Voltage			0.8	V	I_C=2mA Ee=20mW/c㎡
I_{CEO}	Collector Dark Current			100	nA	V_{CE}=10V Ee=0mW/c㎡
T_R	Rise Time (10% to 90%)		15		us	V_{CE} = 5V I_C=1mA R_L=1000Ω
T_F	Fall Time (90% to 10%)		15		us	
$I_{(ON)}$	On State Collector Current	0.35	0.8		mA	V_{CE} = 5V Ee=1mW/c㎡ λ=940nm

Absolute Maximum Ratings at TA=25°C

Parameter	Max.Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature	-40°C To +85°C
Storage Temperature	-40°C To +85°C
Lead Soldering Temperature (>5mm for 5sec)	260°C



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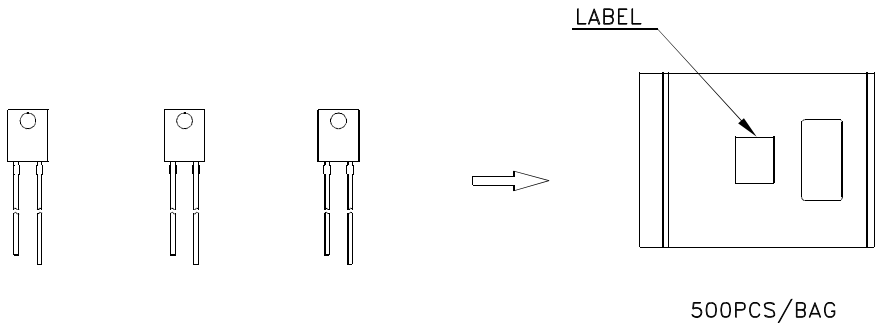
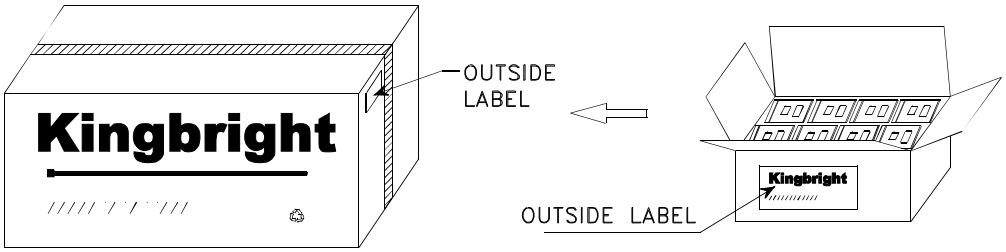
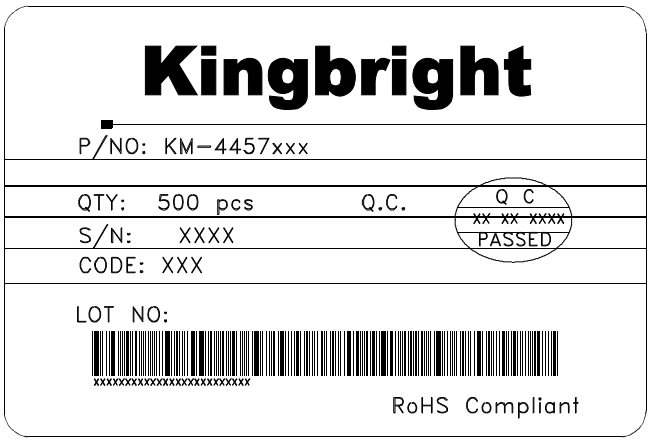
PACKING & LABEL SPECIFICATIONS **KM-4457P3C**





30K/9# BOX

15K/5# BOX



Detailed application notes are listed on our website.
http://www.kingbright.com/application_notes